

4V Drive Pch MOSFET

RW1E025RP

Structure

Silicon P-channel MOSFET

Features

- 1) Low On-resistance.
- 2) Small high power package.
- 3) Low voltage drive.(4V)

Application

Switching

Packaging specifications

	Package	Taping	
Type	Code	T2CR	
	Basic ordering unit (pieces)	8000	
RW1E025RP		0	

● Absolute maximum ratings (Ta = 25°C)

Davis		, Ol	Linette	1.1
Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	-30	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	Continuous	I _D	±2.5	Α
	Pulsed	I _{DP} *1	±10	Α
Source current	Continuous	I _S	-0.5	Α
(Body Diode)	Pulsed	I _{SP} *1	-10	Α
Power dissipation		P _D *2	0.7	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

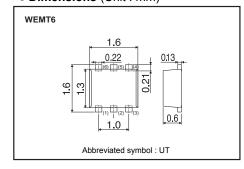
^{*1} Pw≤10µs, Duty cycle≤1%

● Thermal resistance

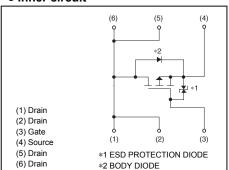
Parameter	Symbol	Limits	Unit
Channel to Ambient	Rth (ch-a)*	179	°C/W

^{*}Mounted on a ceramic board.

● Dimensions (Unit : mm)



• Inner circuit



^{*2} Mounted on a ceramic board.

● Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	1	-	±10	μA	V_{GS} =±20V, V_{DS} =0V
Drain-source breakdown voltage	$V_{(BR)DSS}$	-30	1	-	V	I _D =-1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	-	-	-1	μA	V_{DS} =-30V, V_{GS} =0V
Gate threshold voltage	V _{GS (th)}	-1.0	1	-2.5	V	V_{DS} =-10V, I_{D} =-1mA
Static ducin accuracy an atata		ı	55	75	mΩ	I _D =-2.5A, V _{GS} =-10V
Static drain-source on-state resistance	R _{DS (on)}	ı	85	115		I _D =-1.2A, V _{GS} =-4.5V
		1	95	125		I _D =-1.2A, V _{GS} =-4V
Forward transfer admittance	IY _{fs} I*	1.5	-	-	S	I _D =-2.5A, V _{DS} =-10V
Input capacitance	C _{iss}	1	480	-	pF	V _{DS} =-10V
Output capacitance	C _{oss}	1	70	-	pF	V _{GS} =0V
Reverse transfer capacitance	C _{rss}	1	70	-	pF	f=1MHz
Turn-on delay time	t _{d(on)} *	1	7	-	ns	I _D =-1.2A, V _{DD} ≒-15V
Rise time	t _r *	-	12	-	ns	V _{GS} =-10V
Turn-off delay time	t _{d(off)} *	ı	50	-	ns	R_L =12.5 Ω
Fall time	t _f *	1	22	-	ns	R_G =10 Ω
Total gate charge	Q _g *	-	5.2	-	nC	I _D =-2.5A
Gate-source charge	Q _{gs} *	-	1.6	_	nC	V _{DD} ≒–15V
Gate-drain charge	Q _{gd} *	-	1.6	-	nC	V _{GS} =–5V

^{*}Pulsed

●Body diode characteristics (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Forward Voltage	V _{SD} *	-	-	-1.2	V	I _s =-2.5A, V _{GS} =0V	

^{*}Pulsed

●Electrical characteristic curves (Ta=25°C)

T_a=25°C 10.0V pulsed -4.0V 4 Drain Current: ⊢l_D [A] 3 V_{GS}=-3.0V 2 V_{GS}=-2.8V V_{GS}=-2.5V 0 0 0.2 0.4 0.8

Fig.1 Typical Output Characteristics (I)

Fig.3 Static Drain-Source On-State Resistance vs. Drain Current

Drain-Source Voltage : -V_{DS} [V]

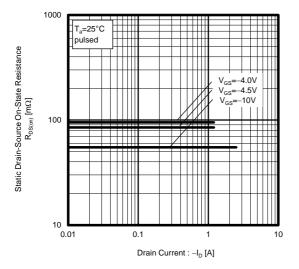


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current

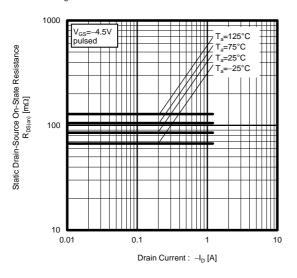


Fig.2 Typical Output Characteristics (II)

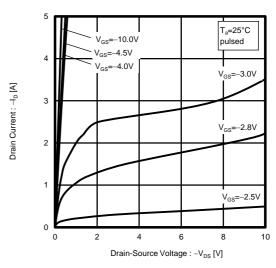


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current

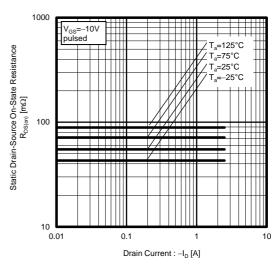


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current

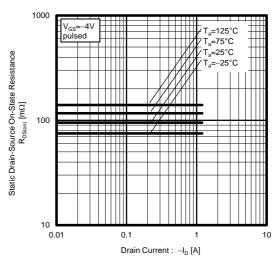


Fig.7 Forward Transfer Admittance vs. Drain Current

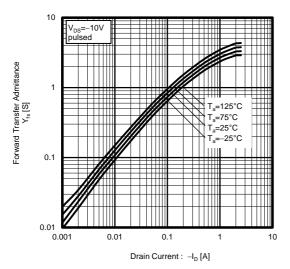


Fig.9 Source Current vs. Source-Drain Voltage

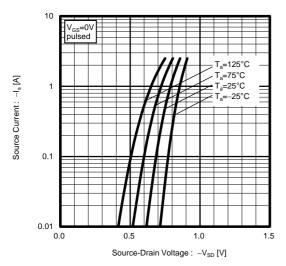


Fig.11 Switching Characteristics

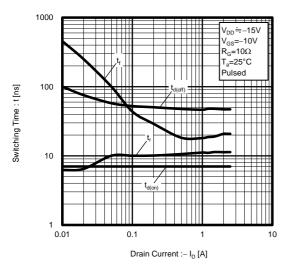


Fig.8 Typical Transfer Characteristics

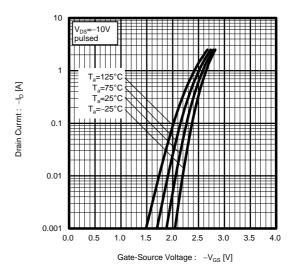


Fig.10 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

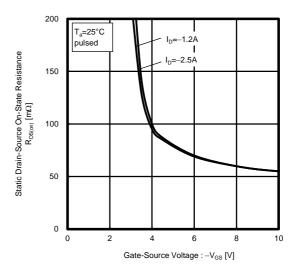


Fig.12 Dynamic Input Characteristics

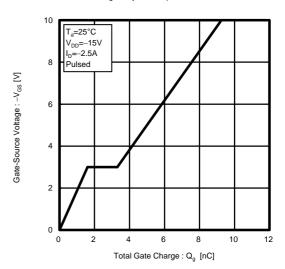
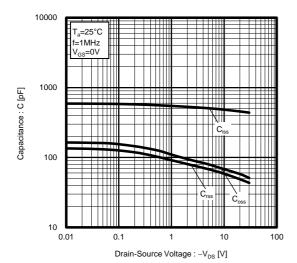


Fig.13 Typical Capacitance vs. Drain-Source Voltage



Measurement circuits

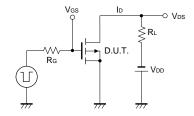


Fig.1-1 Switching Time Measurement Circuit

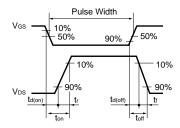


Fig.1-2 Switching Waveforms

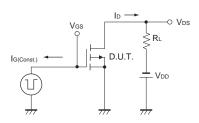


Fig.2-1 Gate Charge Measurement Circuit

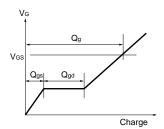


Fig.2-2 Gate Charge Waveform

Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

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